

TOSHIBA Transistor Silicon NPN Epitaxial Type (PCT process)

2SC2716

High Frequency Amplifier Applications

AM High Frequency Amplifier Applications

AM Frequency Converter Applications

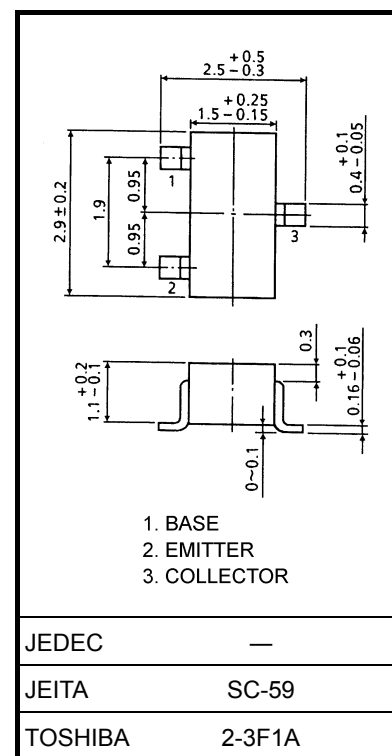
Unit: mm

- Low noise figure: $NF = 3.5\text{dB (max)}$ ($f = 1\text{ MHz}$)

Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Characteristics	Symbol	Rating	Unit
Collector-base voltage	V_{CBO}	35	V
Collector-emitter voltage	V_{CEO}	30	V
Emitter-base voltage	V_{EBO}	4	V
Collector current	I_C	100	mA
Emitter current	I_E	-100	mA
Collector power dissipation	P_C	150	mW
Junction temperature	T_j	125	$^\circ\text{C}$
Storage temperature range	T_{stg}	-55~125	$^\circ\text{C}$

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.012 g (typ.)

Electrical Characteristics ($T_a = 25^\circ\text{C}$)

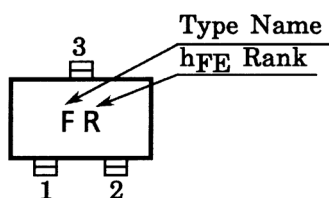
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 20\text{ V}, I_E = 0$	—	—	0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 2\text{ V}, I_C = 0$	—	—	1.0	μA
DC current gain	h_{FE} (Note)	$V_{CE} = 12\text{ V}, I_C = 2\text{ mA}$	40	—	240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	—	—	0.4	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 10\text{ mA}, I_B = 1\text{ mA}$	—	—	1.0	V
Transition frequency	f_T	$V_{CE} = 10\text{ V}, I_C = 2\text{ mA}$	80	120	—	MHz
Reverse transfer capacitance	C_{re}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	2.2	3.0	pF
Collector-base time constant	$C_{c-rbb'}$	$V_{CE} = 10\text{ V}, I_E = -1\text{ mA}, f = 30\text{ MHz}$	—	30	50	ps
Noise figure	NF	$V_{CE} = 10\text{ V}, I_E = -1\text{ mA}, f = 1\text{ MHz}$ $R_g = 50\ \Omega$	—	2.0	3.5	dB

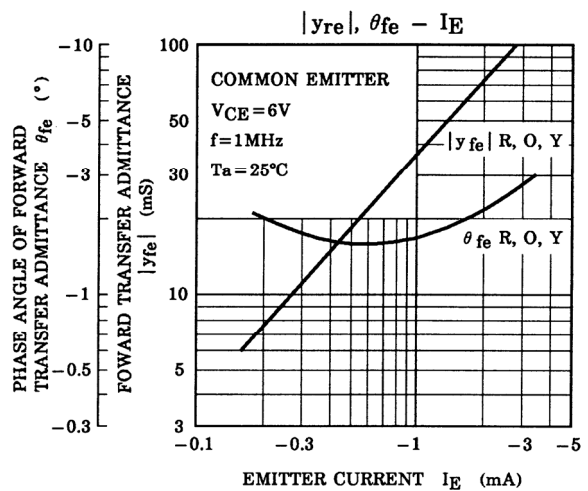
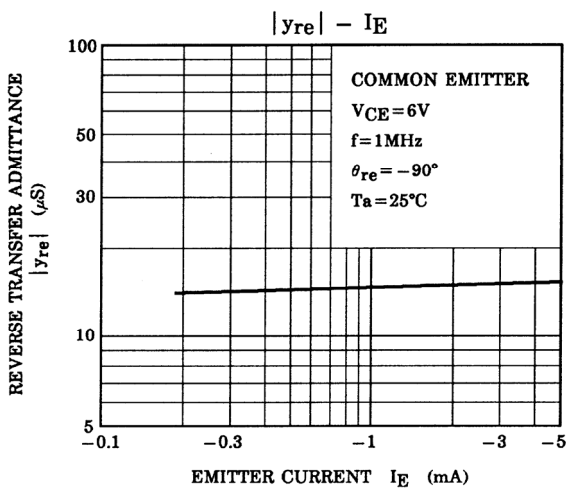
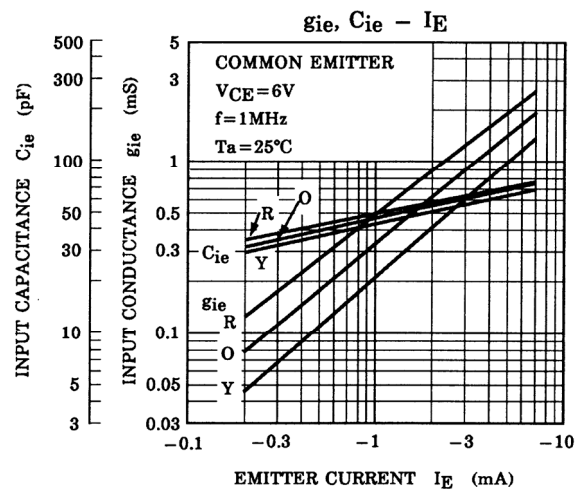
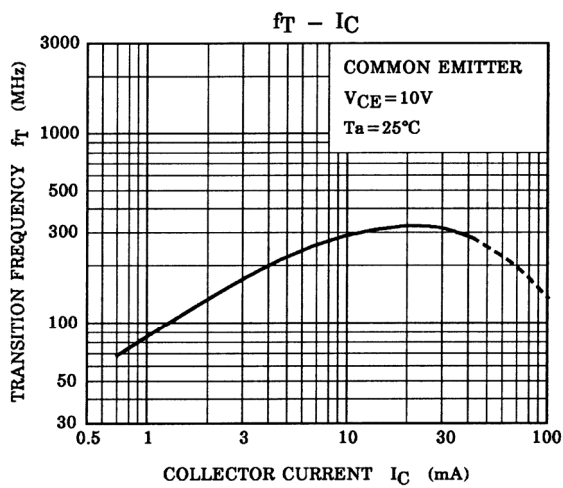
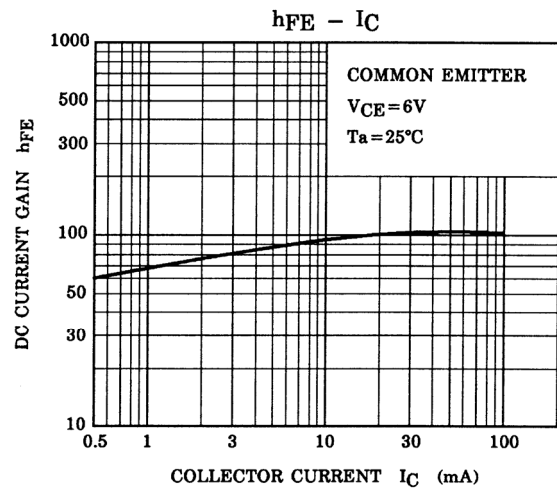
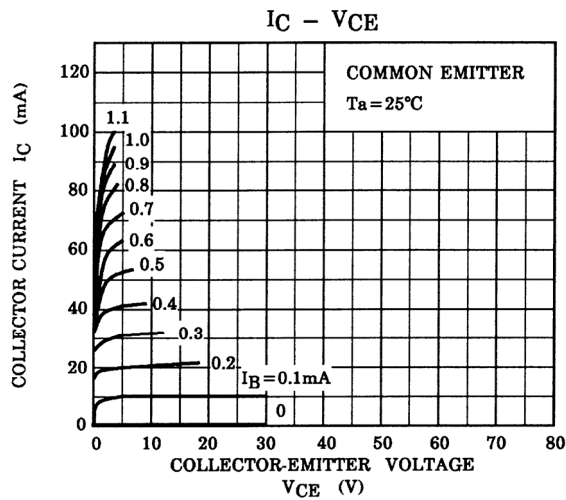
Note: h_{FE} classification R: 40~80, O: 70~140, Y: 120~240

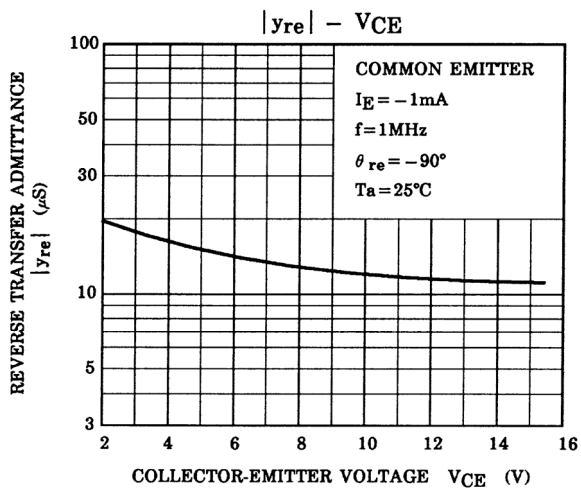
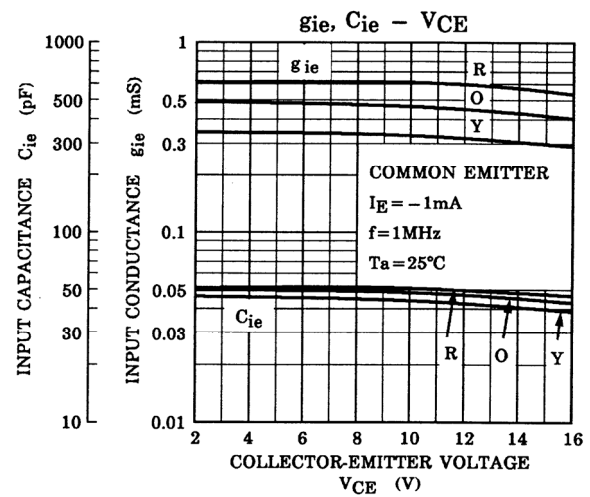
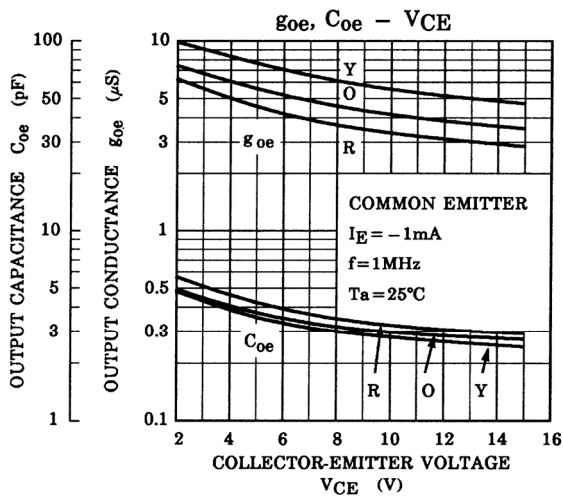
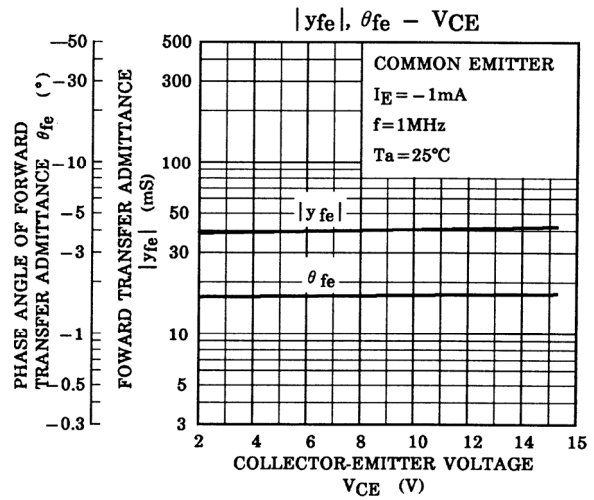
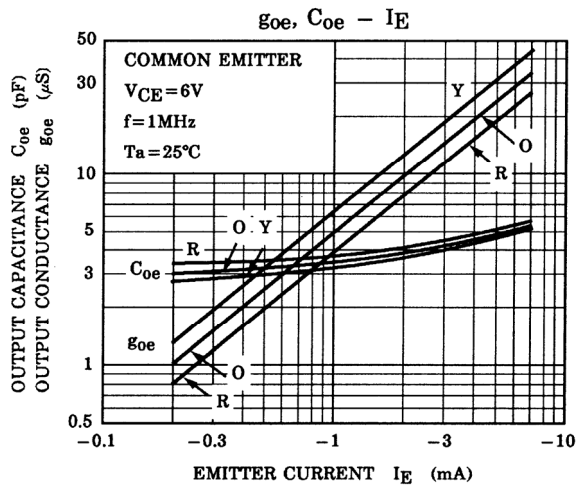
y Parameter (typ.) (common emitter VCE = 6 V, IE = -1 mA, f = 1 MHz)

Characteristics	Symbol	2SC2716-R	2SC2716-O	2SC2716-Y	Unit
Input conductance	g_{ie}	0.5	0.35	0.22	mS
Input capacitance	C_{ie}	50	48	46	pF
Output conductance	g_{oe}	4	5	6.5	μ S
Output capacitance	C_{oe}	3.7	3.4	3.2	pF
Forward transfer admittance	$ y_{fe} $	36	36	36	mS
Phase angle of forward transfer admittance	θ_{fe}	-1.6	-1.6	-1.6	°
Reverse transfer admittance	$ y_{re} $	14	14	14	μ S
Phase angle of reverse transfer admittance	θ_{re}	-90	-90	-90	°

Marking







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20070701-EN GENERAL

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